

EL - 1KL3 · EL - 1KL5

The EL - 1KL3 and 1KL5 are high - power GaAs IREds mounted in durable, hermetically sealed TO - 18 metal can package, which provides years of reliable performance even under demanding conditions such as use outdoors.

FEATURES

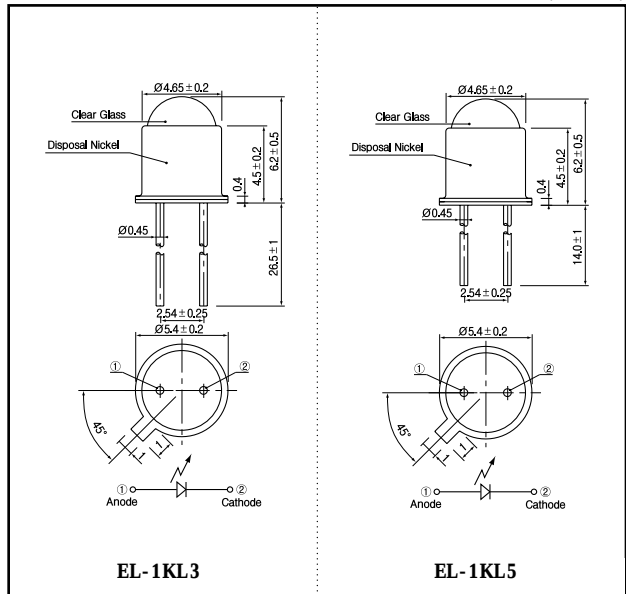
- Narrow beam angle
- Durable
- High reliability in demanding environments

APPLICATIONS

- Optical emitters
- Optical switches
- Encoders
- Smoke sensors

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25 °C)

Item	Symbol	Rating	Unit
Reverse voltage	V_R	5	V
Forward current	I_F	100	mA
Pulse forward current ^{*1}	I_{FP}	1	A
Power dissipation	P_c	170	mW
Operating temp.	$T_{opr.}$	- 40 ~ +100	
Storage temp.	$T_{stg.}$	- 55 ~ +125	
Soldering temp. ^{*2}	$T_{sol.}$	260	

*1. pulse width : t_w 100 μ sec. period : T = 10msec.

*2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

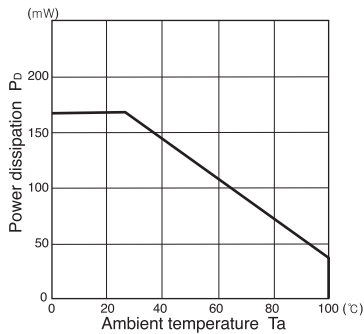
(Ta=25 °C)

Item	Symbol	Conditions	EL - 1KL3			EL - 1KL5			Unit.
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 100\text{mA}$		1.35	1.7		1.35	1.7	V
Reverse current	I_R	$V_R = 5\text{V}$			10			10	μ A
Capacitance	C_t	$f = 1\text{MHz}$		25			25		pF
Radiant intensity	P_o	$I_F = 100\text{mA}$		15			10		mW/sr
Peak emission wavelength	λ_p	$I_F = 100\text{mA}$		940			940		nm
Spectral bandwidth 50%	$\Delta \lambda$	$I_F = 100\text{mA}$		50			50		nm
Half angle	θ			± 8			± 5		deg.

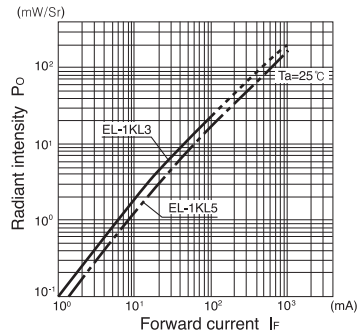
Infrared Emitting Diodes(GaAs)

EL - 1KL3 · EL - 1KL5

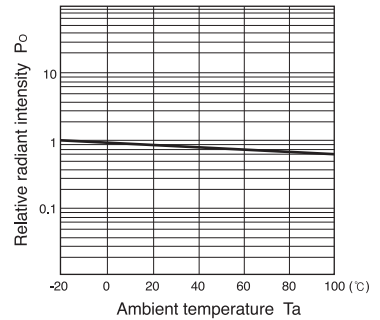
Power dissipation Vs. Ambient temperature



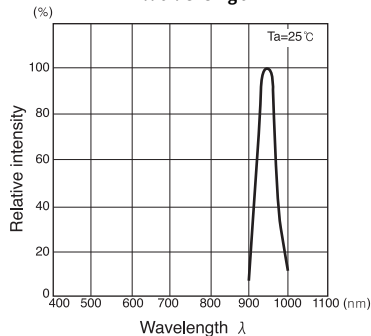
Radiant intensity Vs. Forward current



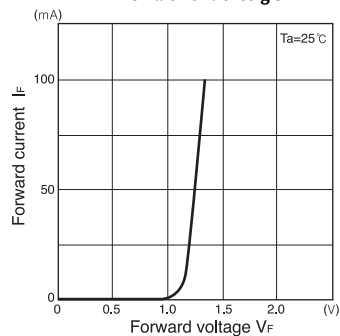
Relative radiant intensity Vs. Ambient temperature



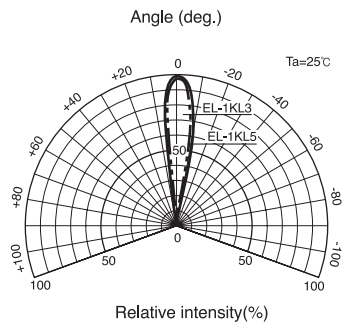
Relative intensity Vs. Wavelength



Forward current Vs. Forward voltage



Radiant Pattern



Relative radiant intensity Vs. Distance

